

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

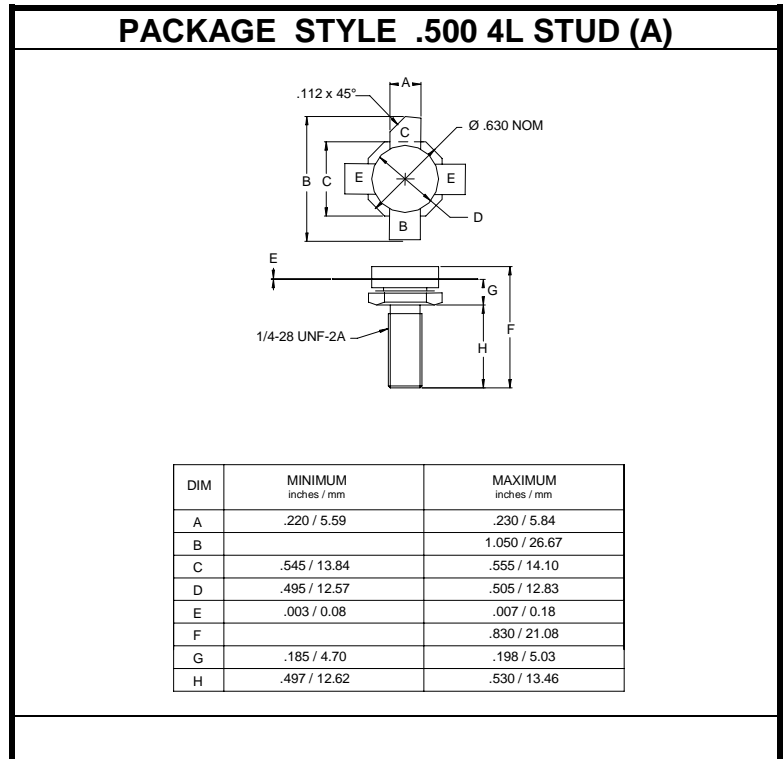
The **ASI BLX14** is Designed for HF and VHF band applications.

FEATURES:

- $P_G = 13$ dB min. at 15 W/1.6 MHz
- $d_3 = -40$ dB typ. at 15 W(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	85 V
V_{EBO}	4.0 V
V_{CEO}	36 V
P_{DISS}	88 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.99 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 25$ mA		85			V
BV_{CER}	$I_C = 25$ mA	$R_{BE} = 5.0$ Ω	85			V
BV_{CEO}	$I_C = 50$ mA		36			V
BV_{EBO}	$I_E = 10$ mA		4.0			V
h_{FE}	$V_{CE} = 6.0$ V	$I_C = 1.4$ A	15		100	---
f_T	$V_{CE} = 20$ V	$I_C = 3.0$ A		250		MHz
C_C	$V_{CB} = 30$ V	$f = 1.0$ MHz		115	125	pF
G_P d_3	$V_{CE} = 28$ V $f = 1.6$ MHz	$I_{CQ} = 2.0$ A $P_{OUT} = 15$ W(PEP)	13	-40		dB dB